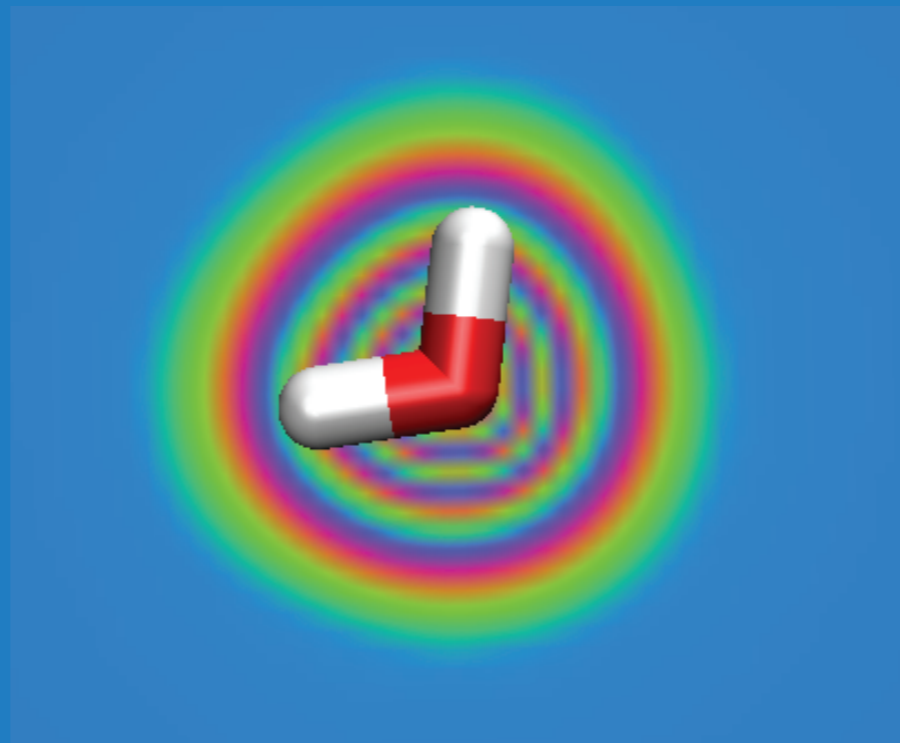


Electronic structure calculations go for a swim

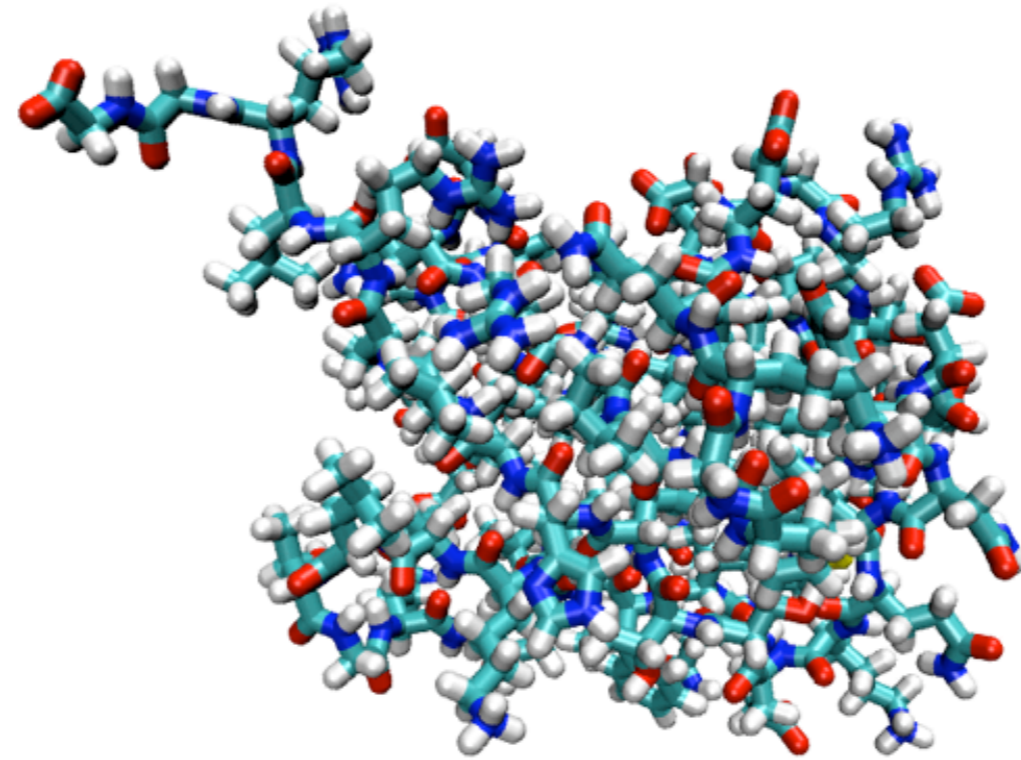


Hatem H. Helal
Electronic structure discussion group
October 31, 2007

Overview

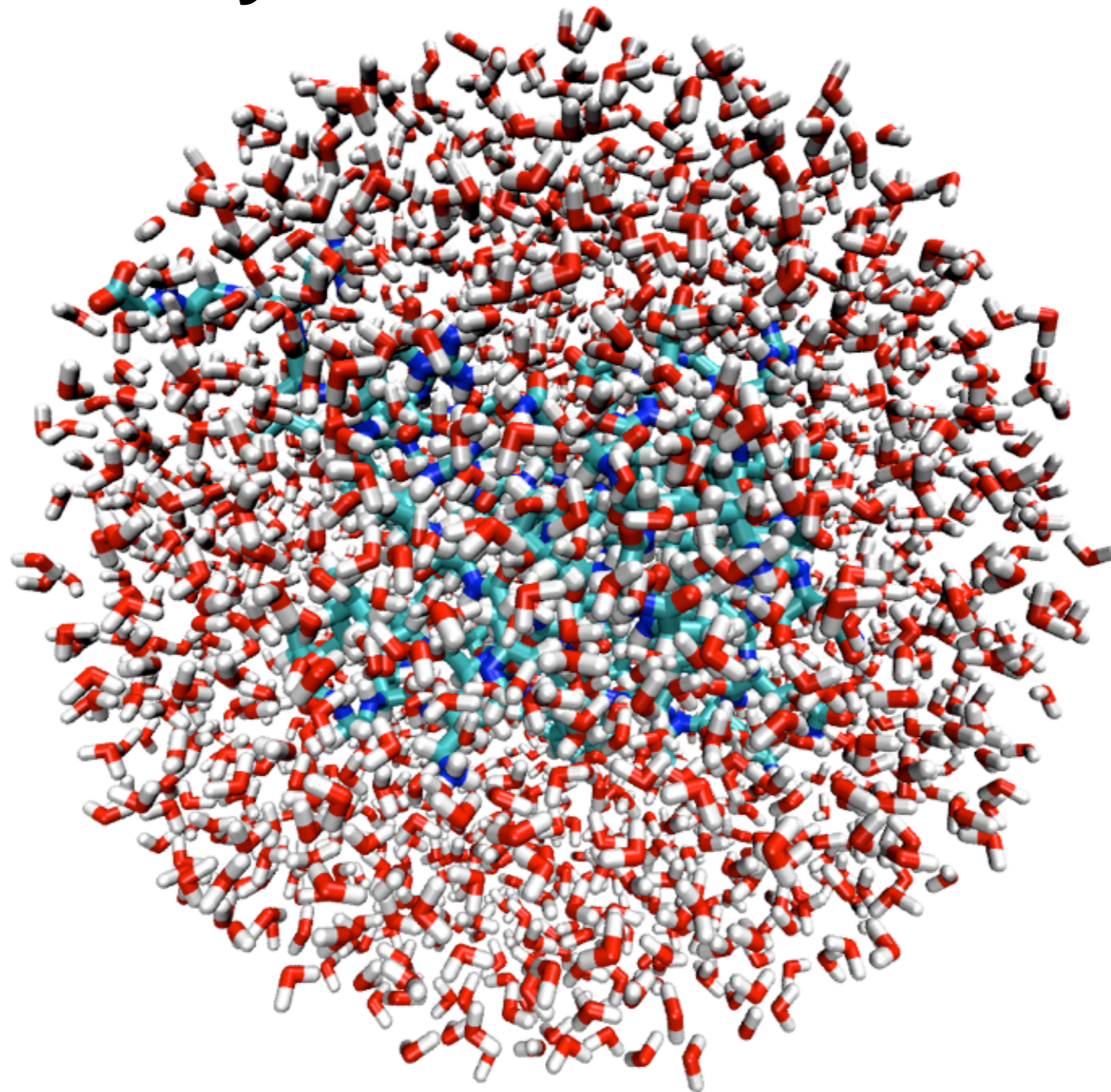
- Why does solvation matter?
- Implicit solvent model for density functional theory calculations
- Real space method for solving the Poisson equation in a dielectric medium

So you want to study solvated systems?



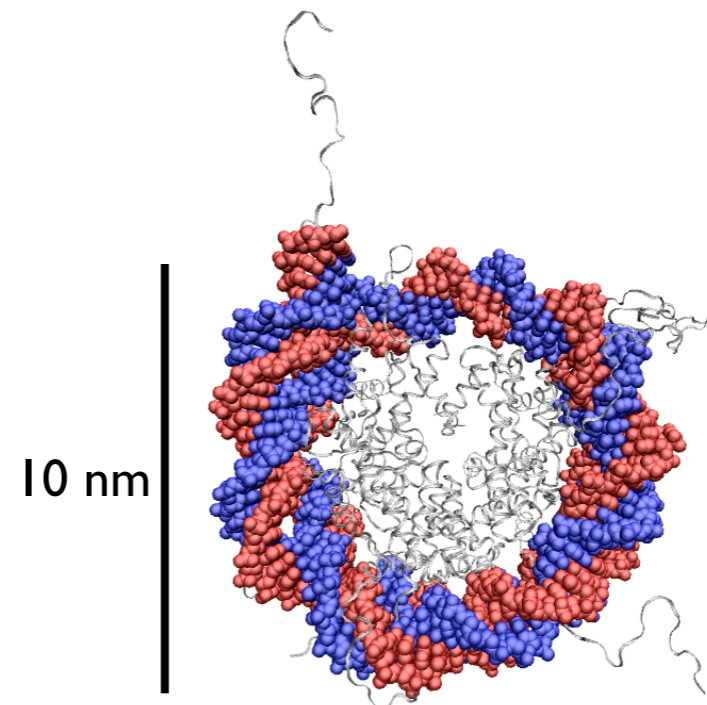
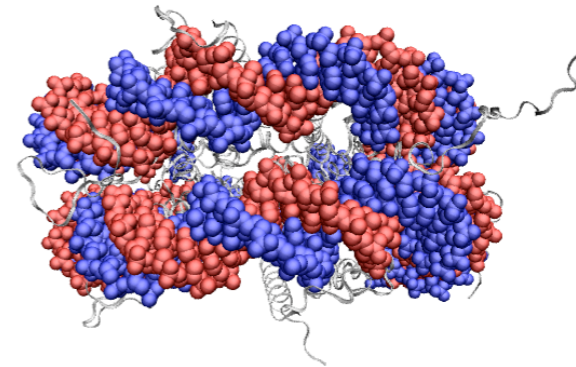
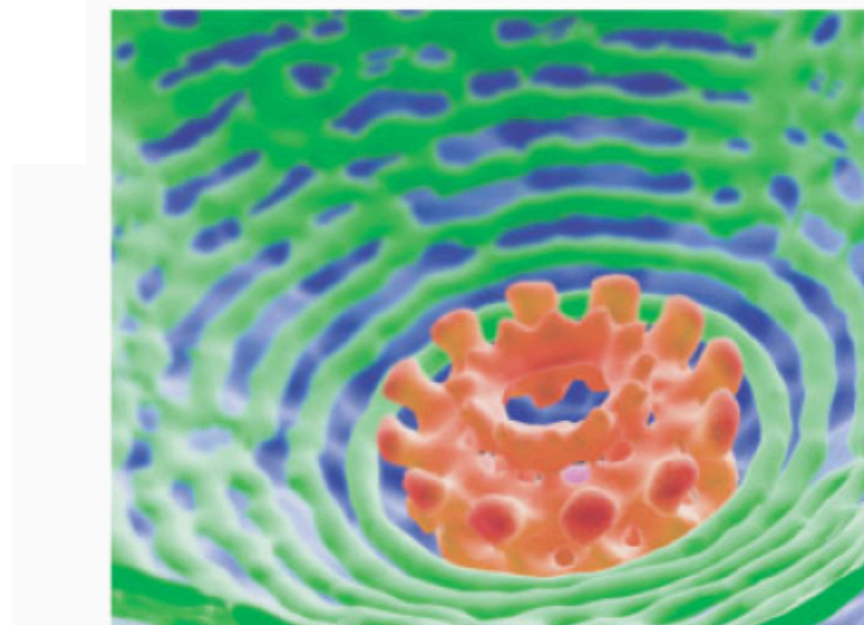
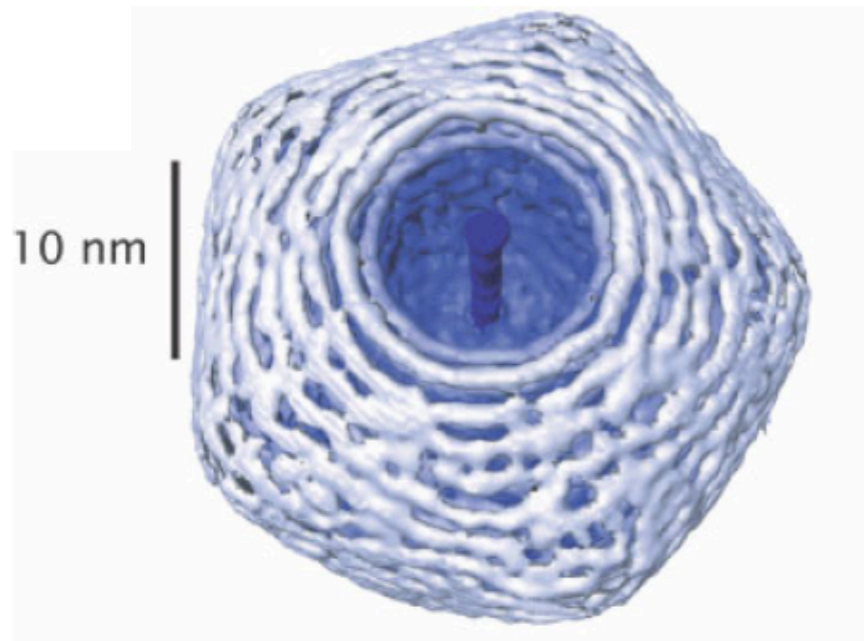
Ubiquitin

Just add water..



Ubiquitin with water

DNA packaging in nature



Defining the free energy of solvation

- Free energy cost of building up a molecule inside a solvent

$$\Delta G_{\text{sol}} = \Delta G_{\text{el}} + \Delta G_{\text{cav}}$$

- The ideal solvent model

- Provides accurate solvation energies without a ridiculous number of parameters
- Uses a natural and straightforward definition of the solvent cavity
- D. A. Scherlis, J. L. Fattebert, F. Gygi et al., J. Chem. Phys. **124** (7), 074103 (2006).
- J. L. Fattebert and F. Gygi, Int. J. Quantum Chem **93** (2), 139 (2003).
- J. L. Fattebert and F. Gygi, J. Comput. Chem. **23** (6), 662 (2002).

The standard DFT approach

$$E[\rho] = T[\rho] + E_{\text{xc}}[\rho] + \int \rho(\mathbf{r})v_{\text{ion}}(\mathbf{r})d\mathbf{r} + \frac{1}{2} \int \rho(\mathbf{r})\phi[\rho]d\mathbf{r}$$

Electrostatic term

- Given the electron density we compute the corresponding electrostatic potential via the Poisson equation:

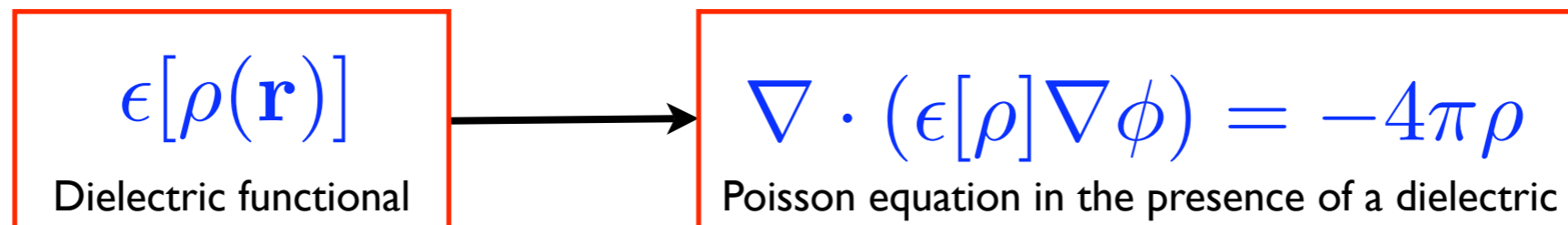
$$\nabla^2 \phi = -4\pi\rho$$

- Under periodic boundary conditions we compute the solution in reciprocal space as:

$$\phi(\mathbf{G}) = \sum_{\mathbf{G}} \frac{-4\pi}{\mathbf{G}^2} \rho(\mathbf{G}) e^{i\mathbf{G}\cdot\mathbf{r}}$$

DFT with implicit solvent

- Replace the *explicit* solvent molecules with a dielectric continuum that *implicitly* replicates the electrostatic interaction between solvent and solute



- From this generalized Poisson equation the electrostatic energy can then be computed as:

$$E_{\text{es}}[\rho] = \frac{1}{8\pi} \int_{\Omega} \epsilon[\rho] |\nabla \phi|^2 d\mathbf{r}$$

DFT with implicit solvent

- The electrostatic contribution to the Kohn-Sham potential is found from the functional derivative:

$$\frac{\delta E_{\text{es}}[\rho]}{\delta \rho} = \phi(\mathbf{r}) + V_{\epsilon}(\mathbf{r})$$

- The additional term arises from the dependence of the dielectric functional on the charge density

$$V_{\epsilon}(\mathbf{r}) \equiv -\frac{1}{8\pi} |\nabla \phi(\mathbf{r})|^2 \frac{\delta \epsilon}{\delta \rho}$$

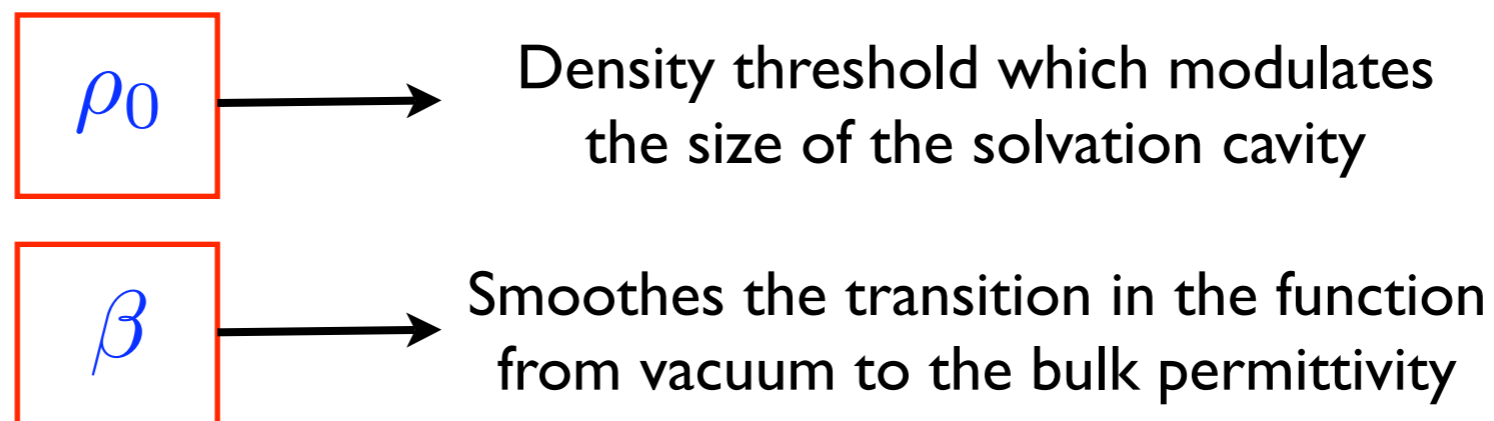
- This results in a tunable solvent cavity as self-consistency is achieved

Properties of the dielectric functional

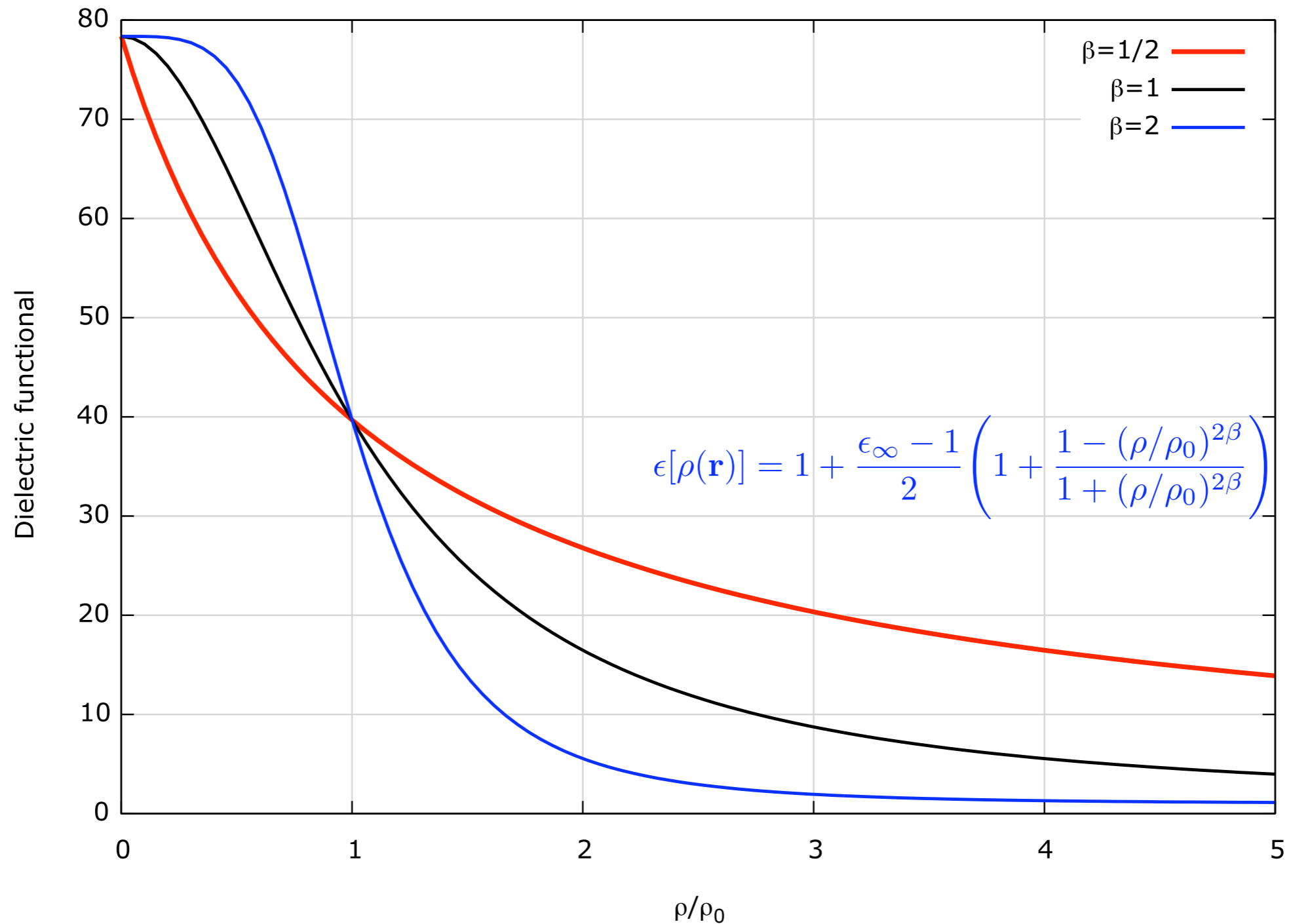
- Uses the electron density to define the solvation cavity
- The dielectric functional is expressed as:

$$\epsilon[\rho(\mathbf{r})] = 1 + \frac{\epsilon_{\infty} - 1}{2} \left(1 + \frac{1 - (\rho/\rho_0)^{2\beta}}{1 + (\rho/\rho_0)^{2\beta}} \right)$$

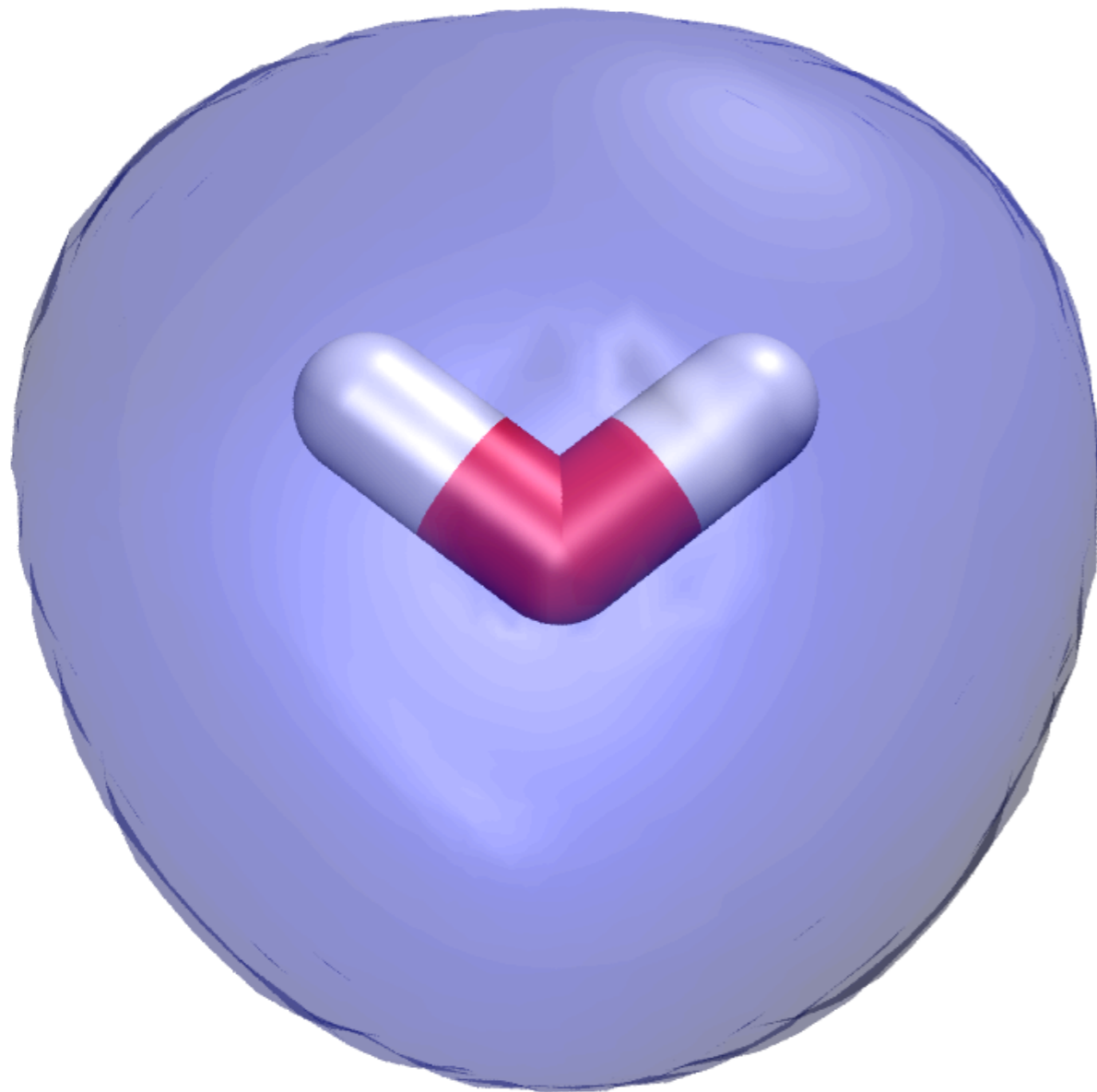
- This results in an implicit solvent model which only depends on two parameters



Dielectric functional for self-consistent solvent cavity



Solvent cavity



$$\epsilon[\rho(\mathbf{r})] = 1.01$$

- Smooth surface of solvation cavity results from natural definition through the charge density
- Dielectric parameters chosen such that the solvation effect on the total energy matches the cohesion energy of liquid water

$$\beta = 1.3 \quad \rho_0 = 0.0004$$

J. L. Fattebert and F. Gygi, J. Comput. Chem. **23** (6), 662 (2002).

Solving the generalized Poisson equation

$$\nabla \cdot (\epsilon[\rho] \nabla \phi) = -4\pi\rho$$
$$\phi(\mathbf{r}) = 0 \text{ on cell boundary}$$

- Solved in real space by multigrid method
- Multigrid properties
 - Finite difference method but makes use of multiple meshes to gain accuracy and speed convergence
 - Scales linearly with the number of grid points
 - Interfaced multigrid solver from 'The Finite Element ToolKit' (<http://www.fetk.org/>) with CASTEP

Cavitation energy

- Simply the amount of work necessary to create the solvent cavity and can be estimated as

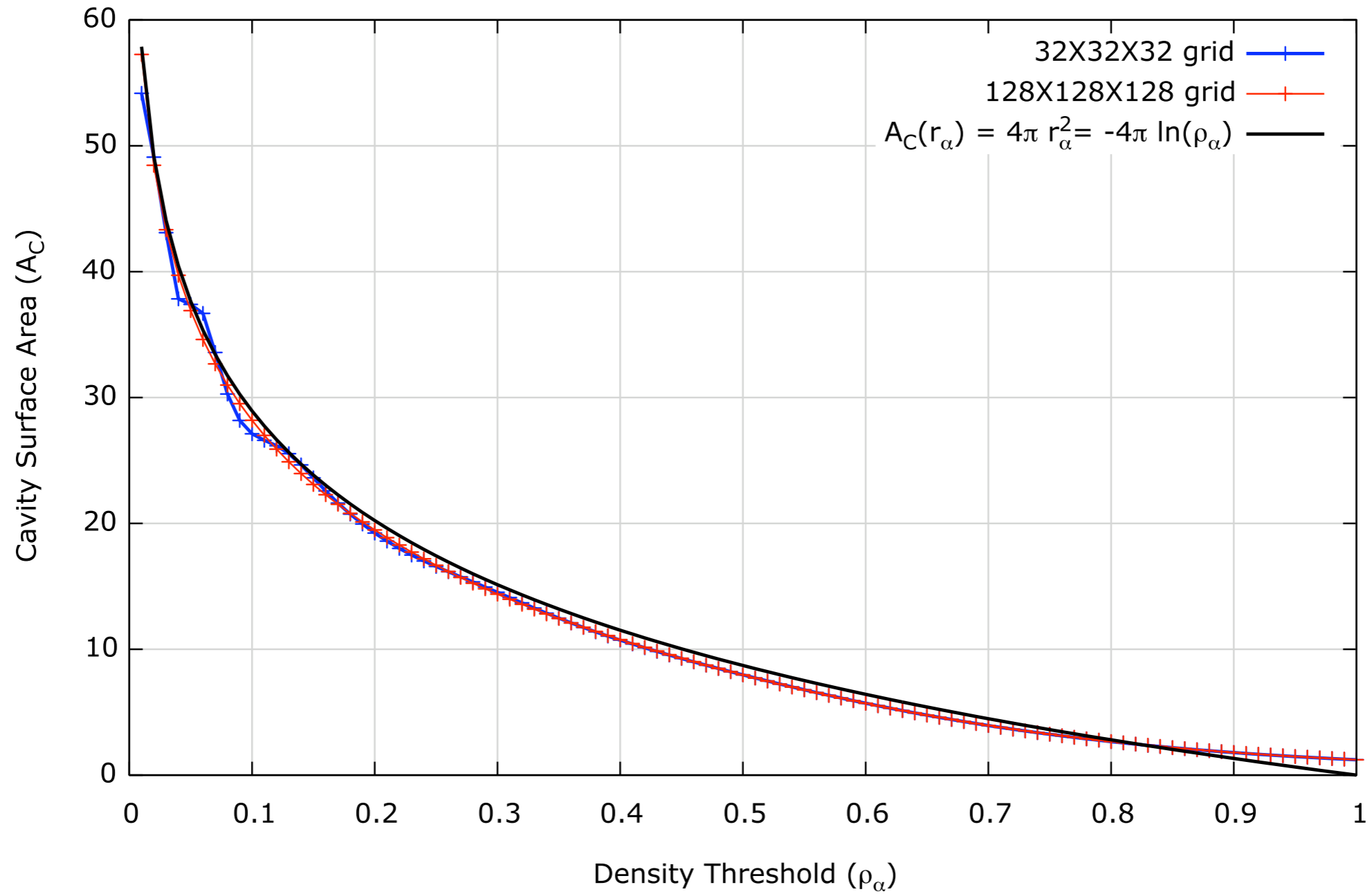
$$\Delta G_{\text{cav}} = \gamma S(\rho_0)$$

- The cavity surface area for a given density threshold (ρ_0) and surface thickness (Δ)

$$S(\rho_0) = \int \frac{|\nabla \rho(\mathbf{r})|}{\Delta} \left(\vartheta_{\rho_0 - \Delta/2}[\rho(\mathbf{r})] - \vartheta_{\rho_0 + \Delta/2}[\rho(\mathbf{r})] \right) d\mathbf{r}$$

- The functional derivative gives an additional potential to include in the Kohn-Sham potential

Surface area of a Gaussian charge density



Summary and a look ahead

- Introduced a general solvation model which effectively relies on only two parameters
- Implementation in CASTEP and eventually ONETEP
 - Interfaced with multigrid solver from 'The Finite Element ToolKit' (<http://www.fetk.org/>) for calculating electrostatic contribution to solvation energy
 - Implementing cavitation contribution to solvation energy
- Eventually using this model to study the bending and packaging of DNA

References and acknowledgments

- **Founding papers**

- D. A. Scherlis, J. L. Fattebert, F. Gygi et al., J. Chem. Phys. **124** (7), 074103 (2006).
- J. L. Fattebert and F. Gygi, Int. J. Quantum Chem **93** (2), 139 (2003)
- J. L. Fattebert and F. Gygi, J. Comput. Chem. **23** (6), 662 (2002).

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